Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	-	-	5	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	6	mA
$V_{T}$	on-state voltage	I <sub>T</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.4	1.7	V
Dynamic chara	acteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	20	-	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 4 A; $dV_{com}/dt$ = 10 V/µs; gate open circuit	1.1	-	-	A/ms
		$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 4 A; $dV_{com}/dt$ = 0.1 V/µs; gate open circuit	4.5	-	-	A/ms

# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		T2
2	T2	main terminal 2		G sym051
3	G	gate		Symost
mb	T2	mounting base; main terminal 2	DPAK (SOT428)	

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
BTA204S-600D	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428		

# 7. Limiting values

## **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 107 ^{\circ}\text{C}$ ; Fig. 1; Fig. 2; Fig. 3	-	4	А
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; Fig. 4; Fig. 5	-	25	А
		full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 16.7 ms	-	27	Α
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	3.1	A²s
dl <sub>T</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 0.2 A	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
$P_{GM}$	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>j</sub>	junction temperature		-	125	°C

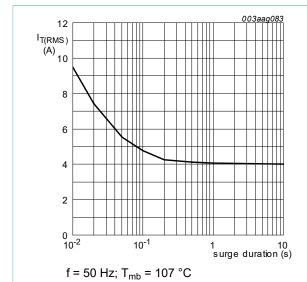


Fig. 1. RMS on-state current as a function of surge duration; maximum values

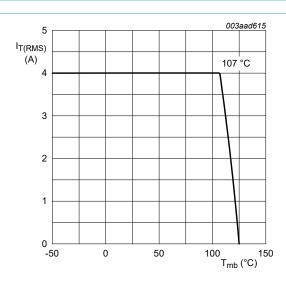


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

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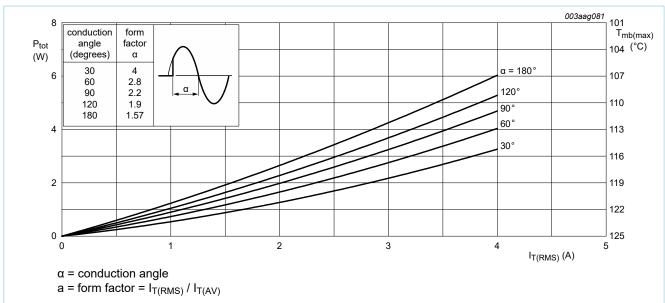


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

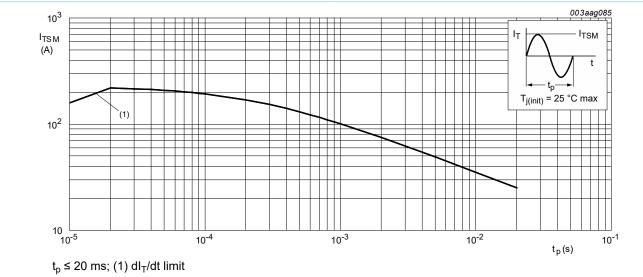


Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

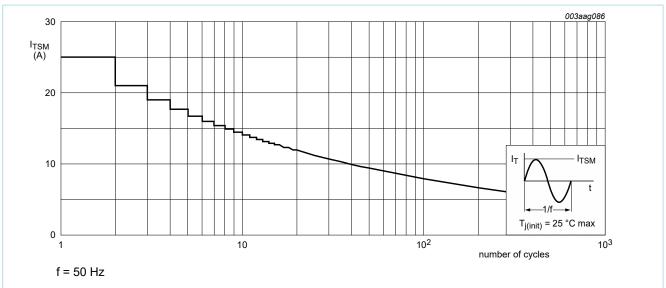
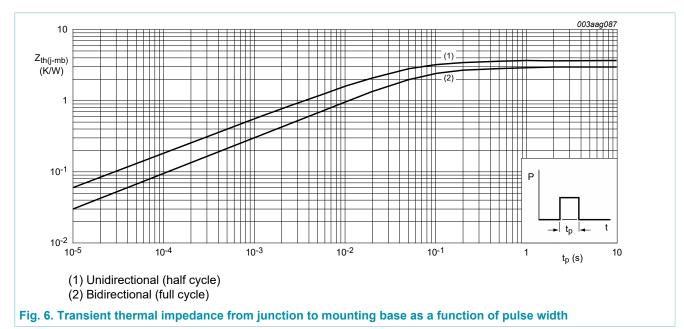


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

## 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	full cycle; Fig. 6	-	-	3	K/W
		half cycle; Fig. 6	-	-	3.7	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	printed circuit board (FR4) mounted	-	75	-	K/W



# 9. Characteristics

#### **Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics				,	
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;} $ $T_j = 25 \text{ °C; } \frac{\text{Fig. 7}}{}$	-	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{ G-;} $ $T_j = 25 \text{ °C; } \frac{\text{Fig. 7}}{}$	-	-	5	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	-	5	mA
IL	latching current	$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2+ G+;$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 8}}{}$	-	-	6	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 8}}{}$	-	-	9	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 8}}{}$	-	-	6	mA
l <sub>н</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	6	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.4	1.7	V
V <sub>GT</sub>	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C; Fig. 11	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic cl	naracteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	20	-	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 4 A; $dV_{com}/dt$ = 10 V/ $\mu$ s; gate open circuit	1.1	-	-	A/ms
		$V_D = 400 \text{ V}; T_j = 125 \text{ °C}; I_{T(RMS)} = 4 \text{ A};$ $dV_{com}/dt = 0.1 \text{ V/}\mu\text{s}; gate open circuit}$	4.5	-	-	A/ms

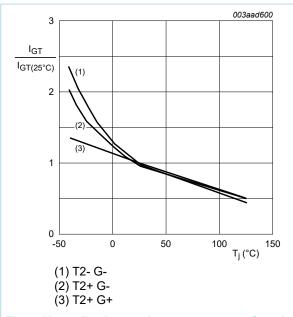


Fig. 7. Normalized gate trigger current as a function of junction temperature

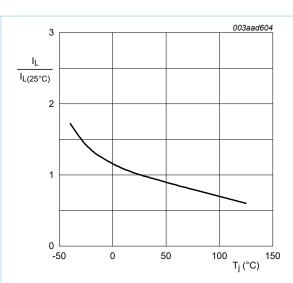


Fig. 8. Normalized latching current as a function of junction temperature

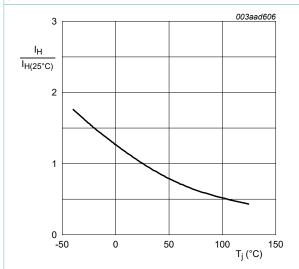
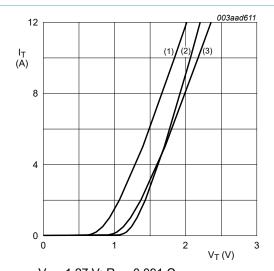
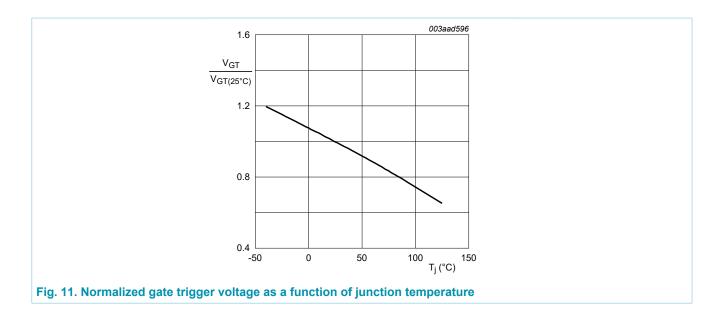


Fig. 9. Normalized holding current as a function of junction temperature

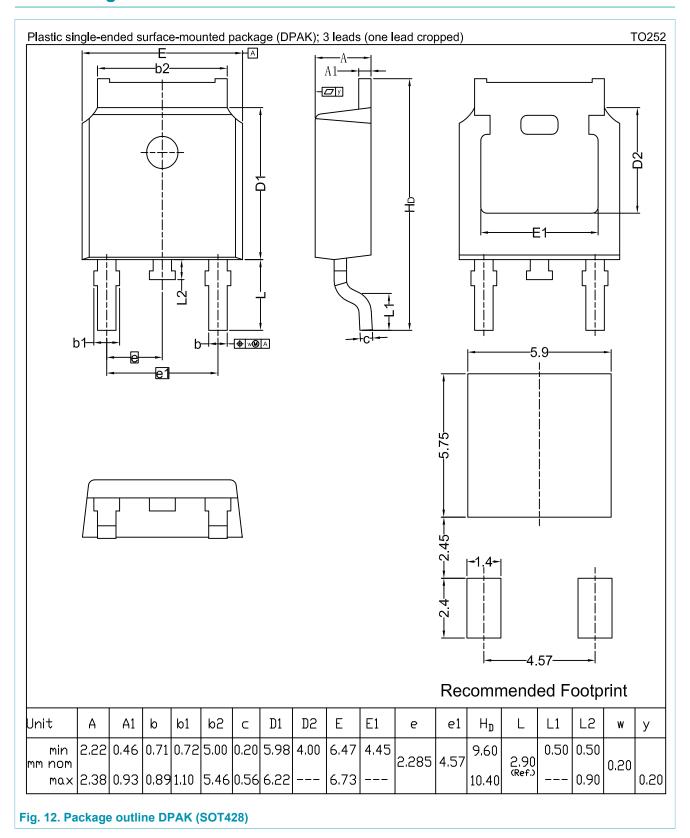


 $V_o$  = 1.27 V;  $R_s$  = 0.091  $\Omega$  (1)  $T_j$  = 125 °C; typical values (2)  $T_j$  = 125 °C; maximum values (3)  $T_j$  = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage



# 10. Package outline



BTA204S-600D

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# 11. Legal information

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